ELECTRONICS, INC.
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NTE637
Schottky Barrier Diode
(Surface Mount)

Absolute Maximum Ratings: (T_a = +25°C, Note 1, unless otherwise specified)

Repetitive Peak Reverse Voltage, V_{RRM} 30V
Average Rectified Forward Current, $I_{F(AV)}$ 200mA
Non−Repetitive Peak Forward Surge Current (Pulse Width = 1.0s), I_{FSM} 600mA
Power Dissipation, P_D 290mW
Storage Temperature Range, T_{STG} . . . . . −55° to +150°C
Operating Junction Temperature, T_J . . . . . −55° to +150°C
Thermal Resistance, Junction−to−Ambient, R_{thJA} . . . . . 430°C/W

Note 1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics: (T_c = +25°C, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Breakdown Voltage	V_R	I_R = 10μA	30	–	–	V
Forward Voltage	V_F	I_F = 0.1mA	–	–	240	mV
		I_F = 1mA	–	–	320	mV
		I_F = 10mA	–	–	400	mV
		I_F = 30mA	–	–	500	mV
		I_F = 100mA	–	–	0.8	V
Reverse Leakage	I_R	V_R = 25V	–	–	2	μA
Total Capacitance	C_T	V_R = 1V, f = 1.0MHz	–	–	10	pF
Reverse Recovery Time	t_{rr}	I_F = I_R = 10mA, I_{RR} = 1.0mA, R_L = 100Ω	–	–	5.0	ns